TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type (U-MOS III)

TPCA8104

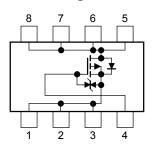
High-Side Switching Applications Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON-resistance: RDS (ON) = 11 m Ω (typ.)
- High forward transfer admittance: $|Y_{fs}| = 50 \text{ S (typ.)}$
- Low leakage current: $IDSS = -10 \mu A (max) (VDS = -60 V)$
- Enhancement mode: V_{th} = -0.8 to -2.0 V (V_{DS} = -10 V, I_D = -1 mA)

Absolute Maximum Ratings (Ta = 25°C)

Ch	naracteristic	C	Symbol	Rating	Unit	
Drain-source v	oltage		V_{DSS}	-60	V	
Drain-gate volt	tage (R _{GS} =	20 kΩ)	V _{DGR} (-60	V	
Gate-source voltage			V _{GSS}	+20	⟨∨	
Drain current	DC	(Note 1)	ID((-40	A	
Diam current	Pulse (Note 1) I _{DP} -120 ssipation (Tc = 25°C) P _D 45	-120				
Drain power dissipation (Tc = 25°C)			(PD	45		
Drain power dissipation (t = 10 s) (Note 2a)			PP	2.8	W	
Drain power dissipation (t = 10 s) (Note 2b)			PD	1.6	$\langle \gamma \rangle$	
Single-pulse avalanche energy (Note 3)			EAS	116	mJ	
Avalanche current			IAR	-40	Α	
Repetitive avalanche energy (Tc = 25°C) (Note 4)			E _{AR}	4.5	mJ	
Channel tempe	nannel temperature		Tah	150	°C	
Storage tempe	rature range	Э	T _{stg}	-55 to 150	°C	

Circuit Configuration



Note: For Notes 1 to 4, see the next page.

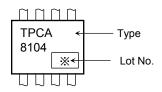
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R _{th (ch-c)}	2.78	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th (ch-a)}	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	78.1	5/ VV

Marking (Note 5)



Note 1: The channel temperature should not exceed 150°C during use.

Note 2: (a) Device mounted on a glass-epoxy board (b) Device mounted on a glass-epoxy board (b)



Note 3: $V_{DD} = -24 \text{ V}$, $T_{Ch} = 25^{\circ}\text{C}$ (initial), $L \neq 0.1 \text{ mH}$, $R_G = 25 \Omega$, $I_{AR} = -40 \text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature.

Note 5: * Weekly code (three digits);





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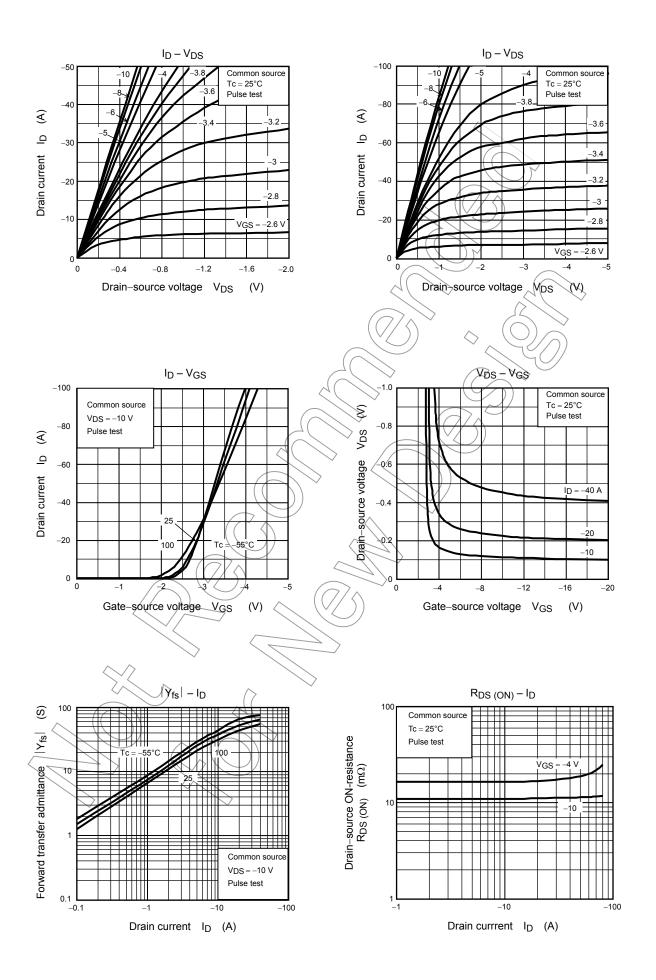
Electrical Characteristics (Ta = 25°C)

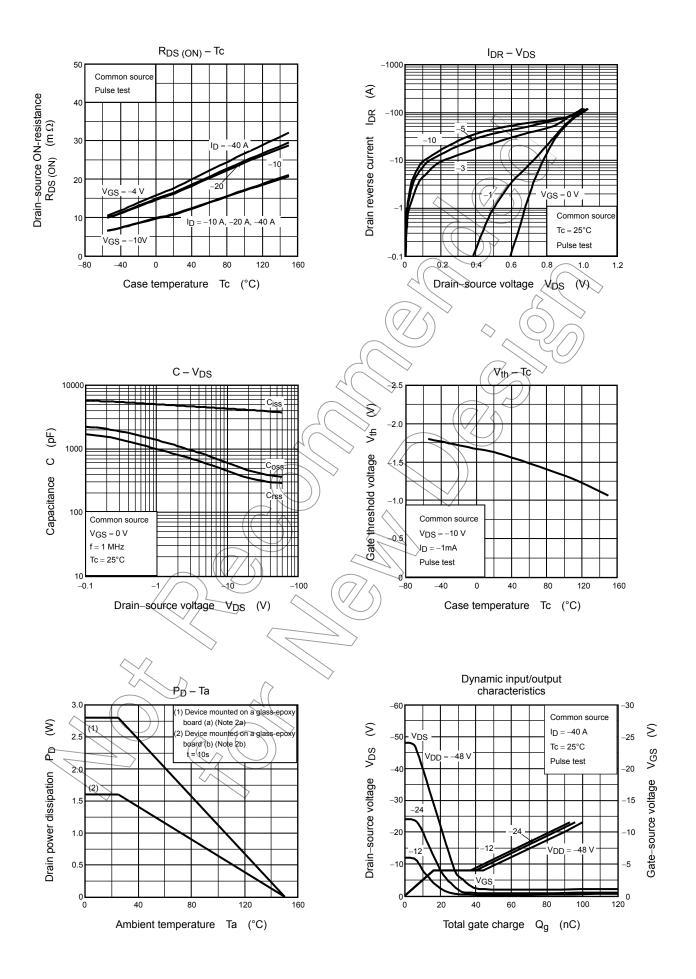
Cha	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μΑ
Drain cutoff curre	nt	I _{DSS}	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$		_	-10	μΑ
Drain-source breakdown		V _{(BR)DSS}	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-60	_	1	· v
voltage	oltage Sate threshold voltage		$I_D = -10 \text{ mA}, V_{GS} = 20 \text{ V}$	35	_	_	
Gate threshold vo	oltage	V _{th}	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$	-0.8) >_	-2.0	V
Drain aguras ON	rociotanos	Б	V _{GS} = -4 V, I _D = -20 A) 	17	24	mO.
Drain-source ON-resistance		R _{DS} (ON)	V _{GS} = -10 V, I _D = -20 Å	\rightarrow	11	16	mΩ
Forward transfer	admittance	Y _{fs}	V _{DS} = -10 V, I _D = -20 A	25	50	_	S
Input capacitance)	C _{iss}		_	4300	_	
Reverse transfer capacitance		C _{rss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, t = 1 \text{ MHz}$	_	450	_	pF
Output capacitance		Coss			600	\searrow	
Switching time	Rise time	t _r	V _{GS} 0 V I _D = -20A Output	_ (10	> _	
	Turn-on time	t _{on}	G \$ 1. G G G G G G G G G G G G G G G G G G		> 20	_	no
	Fall time	t _f	VDD ≈ \(\frac{30}{30}\)\\		60	_	ns
	Turn-off time	toff	Duty \leq 1%, $t_W = 10 \mu s$	_	200	_	
Total gate charge (gate-source plus gate-drain)		(Qg	V _{DD} ≈ -48 V, V _{GS} = -10 V	_	90	_	
Gate-source charge 1		Q _{gs1}	I _D = -40 A	_	16	_	nC
Gate-drain ("Miller") charge		Q _{gd}		_	28	_	

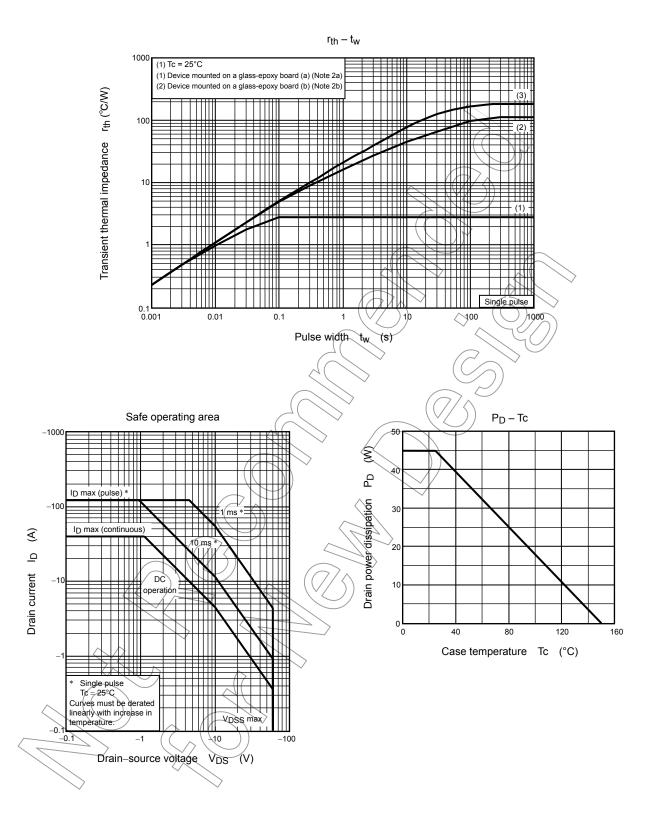
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteris	tic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	^I DRP	<u> </u>	_	_	-120	Α
Forward voltage (diode)		V _{DSF} I _{DR}	= -40 A, V _{GS} = 0 V	_	_	1.2	V









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